

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors



DISCRETE SEMICONDUCTORS

DATA SHEET

BT258 series Thyristors logic level

Product specification

October 2002



NXP Semiconductors Product specification

Thyristors logic level

BT258 series

GENERAL DESCRIPTION

Passivated, sensitive gate thyristors in a plastic envelope, intended for use in general purpose switching and phase control applications. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

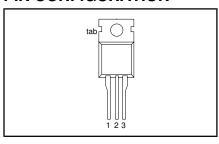
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V _{DRM} , V _{RRM} I _{T(AV)} I _{T(RMS)} I _{TSM}	BT258- Repetitive peak off-state voltages Average on-state current RMS on-state current Non-repetitive peak on-state	500R 500 5 8 75	600R 600 5 8 75	800R 800 5 8 75	V A A A

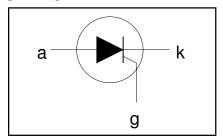
PINNING - TO220AB

PIN	DESCRIPTION
1 cathode	
2	anode
3	gate
tab	anode

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
V_{DRM}, V_{RRM}	Repetitive peak off-state voltages		-	-500R 500 ¹	-600R 600 ¹	-800R 800	٧
$\begin{matrix} \mathbf{I}_{T(AV)} \\ \mathbf{I}_{T(RMS)} \\ \mathbf{I}_{TSM} \end{matrix}$	Average on-state current RMS on-state current Non-repetitive peak on-state current	half sine wave; $T_{mb} \le 111 ^{\circ}\text{C}$ all conduction angles half sine wave; $T_{j} = 25 ^{\circ}\text{C}$ prior to surge	-	5 8		A A	
l²t dl _⊤ /dt	I ² t for fusing Repetitive rate of rise of on-state current after	t = 10 ms t = 8.3 ms t = 10 ms $l_{TM} = 10 \text{ A}; l_G = 50 \text{ mA};$ $dl_G/dt = 50 \text{ mA}/\mu s$	- - -		75 82 28 50		Α Α Α²s Α/μs
I _{GM} V _{RGM} P _{GM} P _{G(AV)} T _{stg} T _j	triggering Peak gate current Peak reverse gate voltage Peak gate power Average gate power Storage temperature Operating junction temperature	over any 20 ms period	- - - -40 -		2 5 5 0.5 150 125 ²		√>\$\$¢¢

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 $A/\mu s$.

² Note: Operation above 110°C may require the use of a gate to cathode resistor of $1k\Omega$ or less.

NXP Semiconductors Product specification

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-mb}	Thermal resistance		-	-	2.0	K/W
R _{th j-a}	junction to mounting base Thermal resistance junction to ambient	in free air	-	60	-	K/W

STATIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{GT}	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$	-	50	200	μΑ
I _L	Latching current	$V_{\rm D} = 12 \text{ V}; I_{\rm GT} = 0.1 \text{ A}$	-	0.4	10	mA
l I _H	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	0.3	6	mA
$V_{T}^{I_{H}}$	On-state voltage	$I_{T} = 16 \text{ A}$	-	1.3	1.6	V
V _{GT}	Gate trigger voltage	$\dot{V}_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$	-	0.4	1.5	V
_ ~.		$V_D = V_{DRM(max)}$; $I_T = 0.1 A$; $T_j = 110 °C$	0.1	0.2	-	V
I_D, I_R	Off-state leakage current	$V_D = V_{DRM(max)}^{SHM(max)}; V_R = V_{RRM(max)}; T_j = 125 °C$	-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

 $T_j = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV _D /dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125 °C;$ exponential waveform; $R_{GK} = 100 \Omega$	50	100	-	V/µs
t _{gt}	Gate controlled turn-on time	$I_{TM} = 10 \text{ A}; V_D = V_{DRM(max)}; I_G = 5 \text{ mA}; dI_G/dt = 0.2 \text{ A/µs}$	-	2	-	μs
t _q	Circuit commutated turn-off time	$ \begin{array}{l} V_{D} = 67\% \ V_{DRM(max)}; \ T_{j} = 125 \ ^{\circ}C; \\ I_{TM} = 12 \ A; \ V_{R} = 24 \ V; \ dI_{TM}/dt = 10 \ A/\mu s; \\ dV_{D}/dt = 2 \ V/\mu s; \ R_{GK} = 1 \ k\Omega \end{array} $	-	100	-	μs

NXP Semiconductors Product specification

Thyristors logic level

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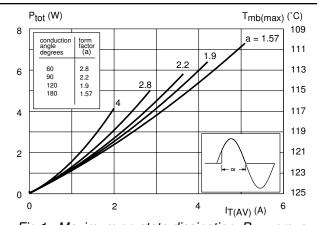


Fig.1. Maximum on-state dissipation, P_{tot} , versus average on-state current, $I_{T(AV)}$, where $a = form \ factor = I_{T(RMS)}/I_{T(AV)}$.

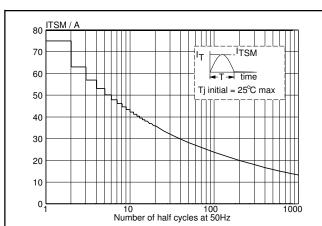


Fig.4. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, f = 50 Hz.

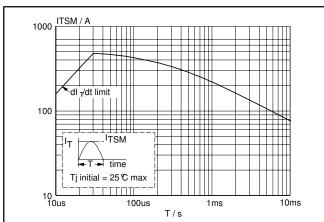


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 10$ ms.

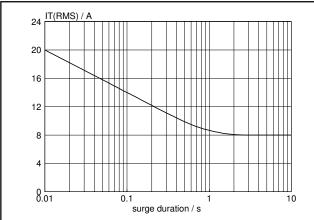


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{mb} \le 111 ^{\circ}\text{C}$.

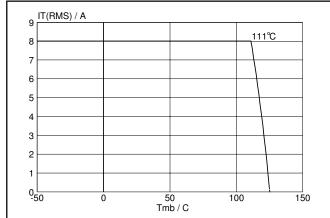
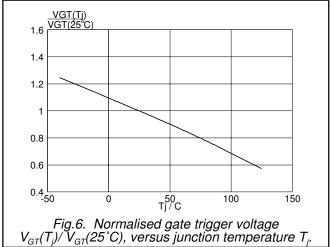


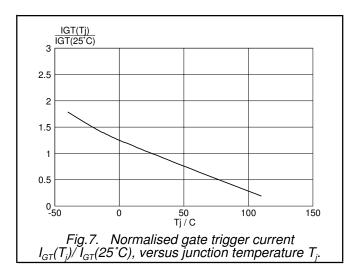
Fig.3. Maximum permissible rms current $I_{T(RMS)}$, versus mounting base temperature T_{mb} .



NXP Semiconductors Product specification

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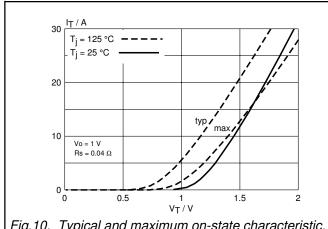
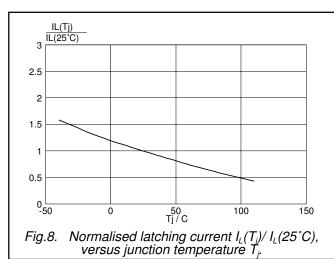
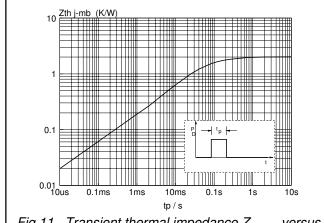


Fig. 10. Typical and maximum on-state characteristic.





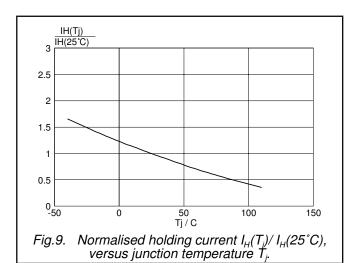


Fig.11. Transient thermal impedance $Z_{th j-mb}$, versus pulse width t_o.

1000 dVD/dt (V/us

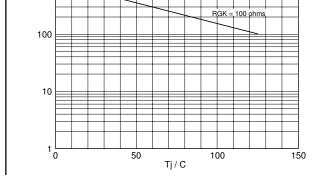


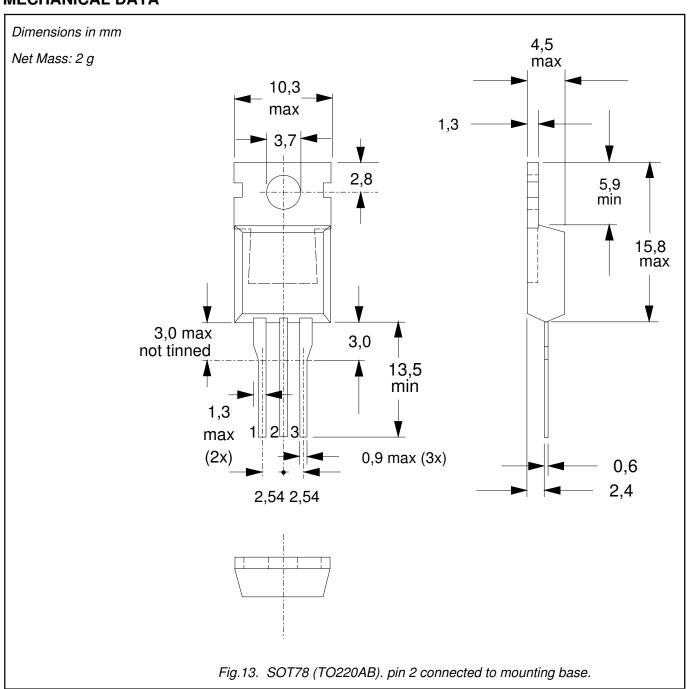
Fig.12. Typical, critical rate of rise of off-state voltage, dV_D/dt versus junction temperature $T_{j\cdot}$

NXP Semiconductors Product specification

Thyristors logic level

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MECHANICAL DATA



- Notes
 1. Refer to mounting instructions for SOT78 (TO220) envelopes.
 2. Epoxy meets UL94 V0 at 1/8".

Legal information

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet Production		This document contains the product specification.

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